

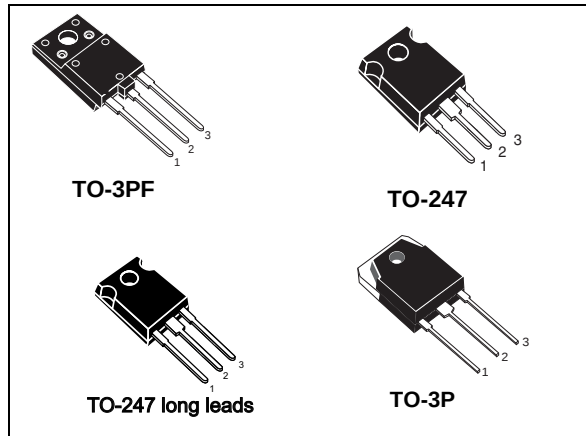
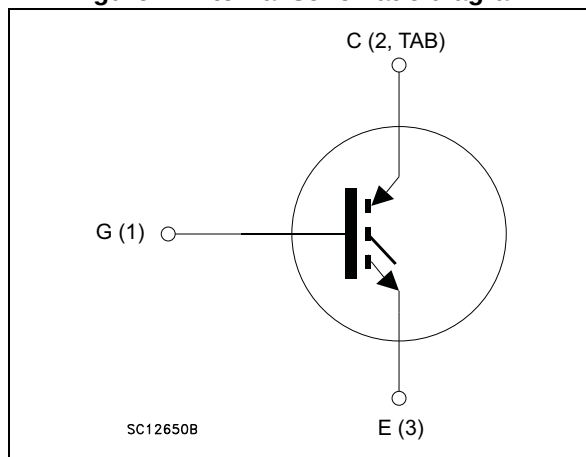


Figure 1. Internal schematic diagram



Features

- Maximum junction temperature: $T_J = 175\text{ }^{\circ}\text{C}$
- High speed switching series
- Minimized tail current
- Very low saturation voltage: $V_{CE(sat)} = 1.6\text{ V}$ (typ.) @ $I_C = 40\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance

Applications

- Photovoltaic inverters
- High frequency converters

Description

These devices are IGBTs developed using an advanced proprietary trench gate and field-stop structure. The device is part of the new HB series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of any frequency converter. Furthermore, a slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1. Device summary

Order code	Marking	Package	Packing
STGFW40H65FB	GFW40H65FB	TO-3PF	Tube
STGW40H65FB	GW40H65FB	TO-247	Tube
STGWA40H65FB	G40H65FB	TO-247 long leads	Tube
STGWT40H65FB	GWT40H65FB	TO-3P	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-247, TO-247 long leads TO-3P	TO-3PF	
V_{CES}	Collector-emitter voltage ($V_{GE} = 0$)	650		V
I_C	Continuous collector current at $T_C = 25\text{ °C}$	80		A
I_C	Continuous collector current at $T_C = 100\text{ °C}$	40		A
$I_{CP}^{(1)}$	Pulsed collector current	160		A
V_{GE}	Gate-emitter voltage	±20		V
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	283	62.5	W
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$; $T_C = 25\text{ °C}$)		3.5	kV
T_{STG}	Storage temperature range	- 55 to 150		°C
T_J	Operating junction temperature range	- 55 to 175		°C

1. Pulse width limited by maximum junction temperature.

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-247, TO-247 long leads TO-3P	TO-3PF	
R_{thJC}	Thermal resistance junction-case	0.53	2.4	°C/W
R_{thJA}	Thermal resistance junction-ambient	50		°C/W

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 2\text{ mA}$	650			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$		1.6	2.0	V
		$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$ $T_J = 125\text{ °C}$		1.7		
		$V_{GE} = 15\text{ V}$, $I_C = 40\text{ A}$ $T_J = 175\text{ °C}$		1.8		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$, $I_C = 1\text{ mA}$	5	6	7	V
I_{CES}	Collector cut-off current ($V_{GE} = 0$)	$V_{CE} = 650\text{ V}$			25	μA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 250	nA

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$	-	5412	-	pF
C_{oes}	Output capacitance		-	198	-	pF
C_{res}	Reverse transfer capacitance		-	107	-	pF
Q_g	Total gate charge	$V_{CC} = 520\text{ V}$, $I_C = 40\text{ A}$, $V_{GE} = 15\text{ V}$, see Figure 27	-	210	-	nC
Q_{ge}	Gate-emitter charge		-	39	-	nC
Q_{gc}	Gate-collector charge		-	82	-	nC

Table 6. Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $R_G = 5\ \Omega$, $V_{GE} = 15\text{ V}$, see Figure 26	-	40	-	ns
t_r	Current rise time		-	13	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	2413	-	A/ μ s
$t_{d(off)}$	Turn-off delay time		-	142	-	ns
t_f	Current fall time		-	27	-	ns
$E_{on}^{(1)}$	Turn-on switching energy		-	498	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy		-	363	-	μ J
E_{ts}	Total switching energy		-	861	-	μ J
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$, $I_C = 40\text{ A}$, $R_G = 5\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$, see Figure 26	-	38	-	ns
t_r	Current rise time		-	14	-	ns
$(di/dt)_{on}$	Turn-on current slope		-	2186	-	A/ μ s
$t_{d(off)}$	Turn-off delay time		-	141	-	ns
t_f	Current fall time		-	61	-	ns
$E_{on}^{(1)}$	Turn-on switching energy		-	1417	-	μ J
$E_{off}^{(2)}$	Turn-off switching energy		-	764	-	μ J
E_{ts}	Total switching energy		-	2181	-	μ J

1. Energy losses including the reverse recovery of the external diode. The diode is the same of the co-packed STGW40H65DFB.
2. Turn-off losses including the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature for TO-247,TO-247 long leads and TO-3P

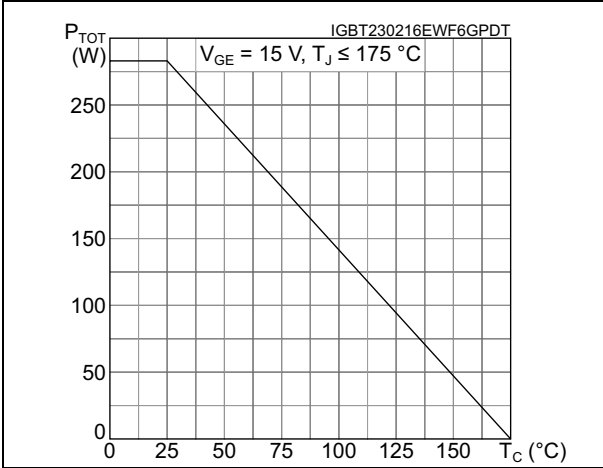


Figure 3. Collector current vs. case temperature for TO-247,TO-247 long leads and TO-3P

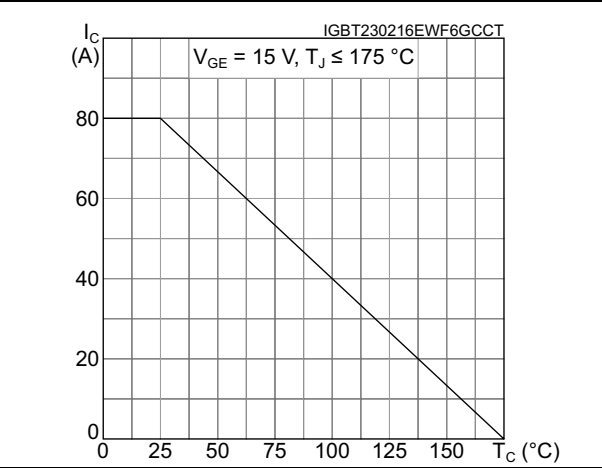


Figure 4. Power dissipation vs. case temperature for TO-3PF

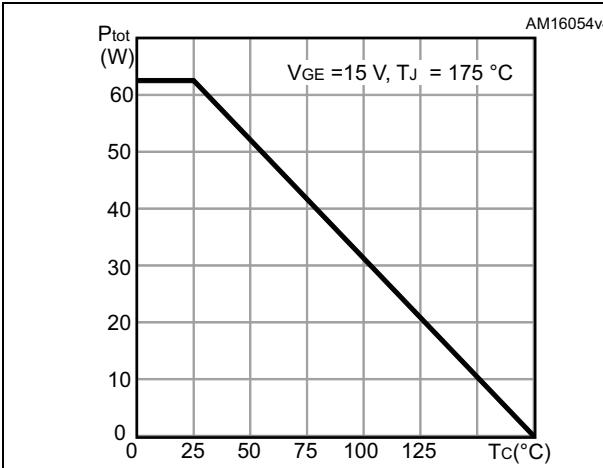


Figure 5. Collector current vs. case temperature for TO-3PF

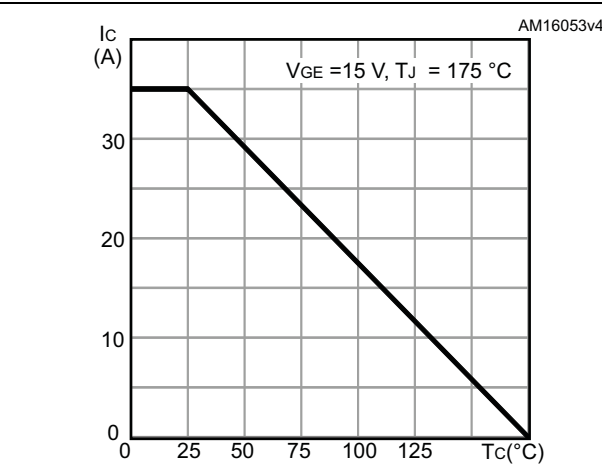


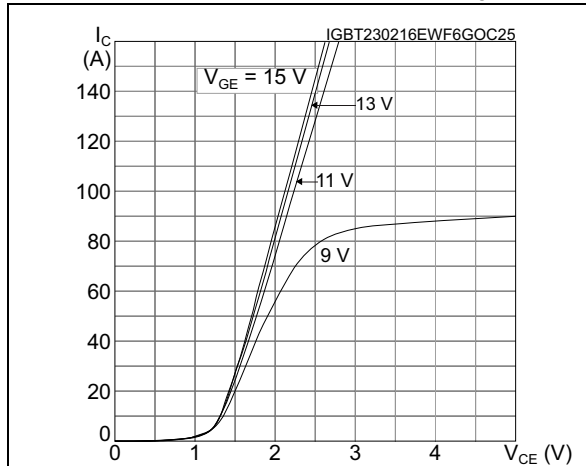
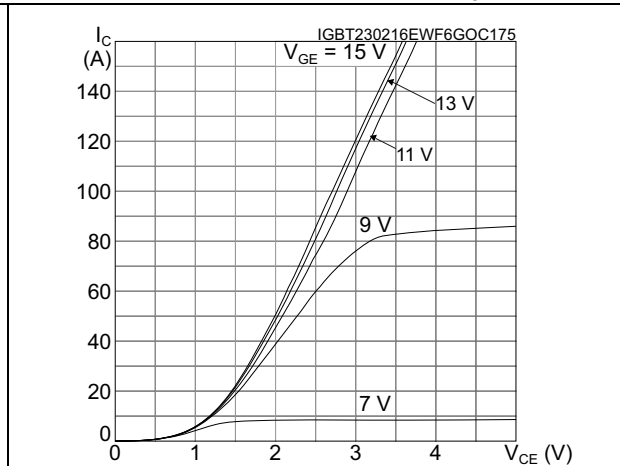
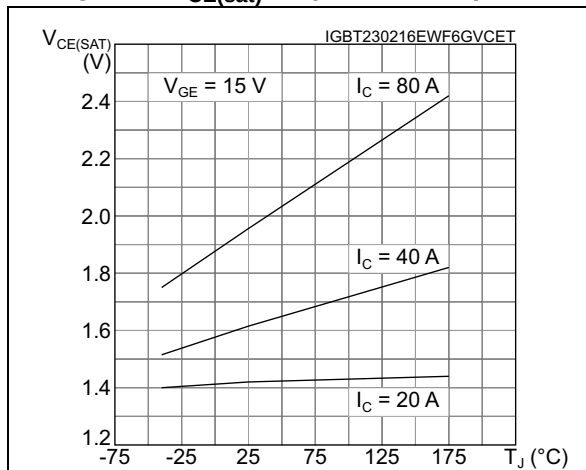
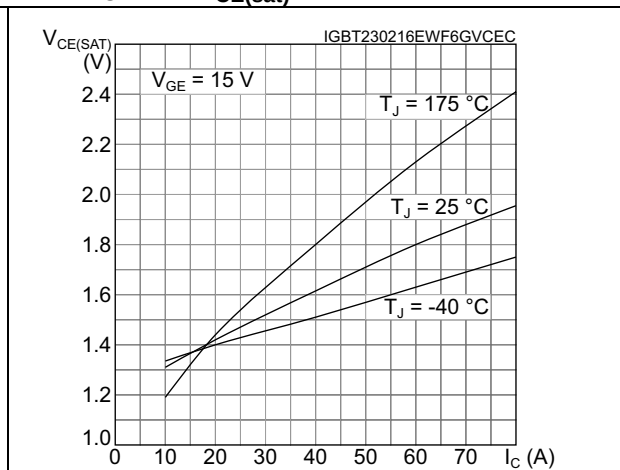
Figure 6. Output characteristics ($T_J = 25^\circ\text{C}$)

Figure 7. Output characteristics ($T_J = 175^\circ\text{C}$)

Figure 8. $V_{CE(sat)}$ vs. junction temperature

Figure 9. $V_{CE(sat)}$ vs. collector current


Figure 10. Collector current vs. switching frequency for TO-247, TO-247 long leads and TO-3P

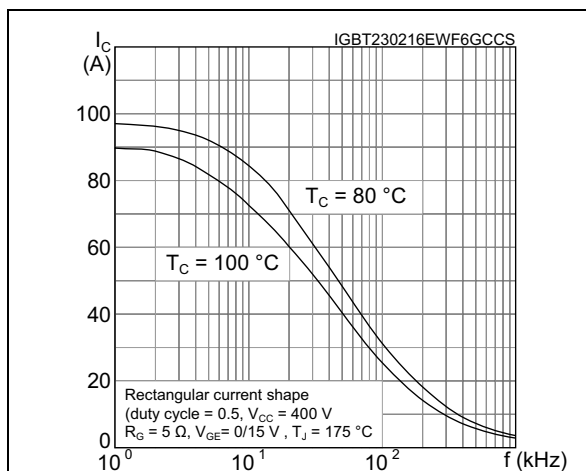


Figure 11. Collector current vs. switching frequency for TO-3PF

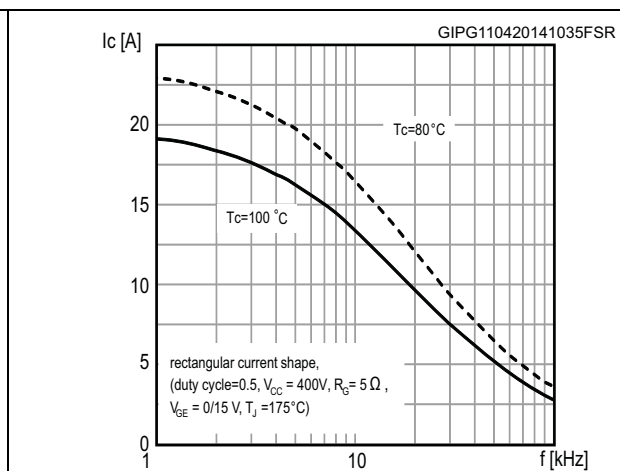


Figure 12. Forward bias safe operating area for TO-247,TO-247 long leads and TO-3P

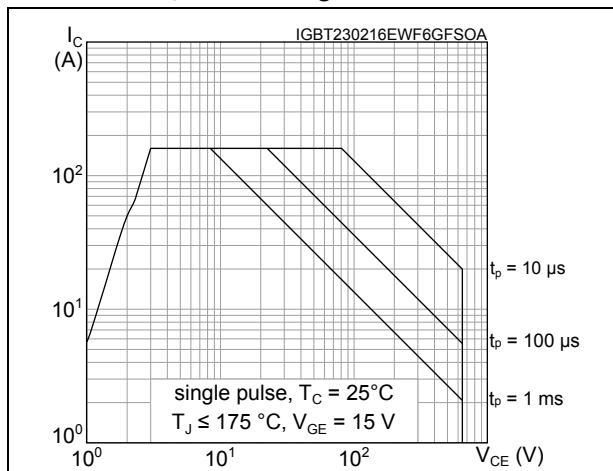


Figure 13. Forward bias safe operating area for TO-3PF

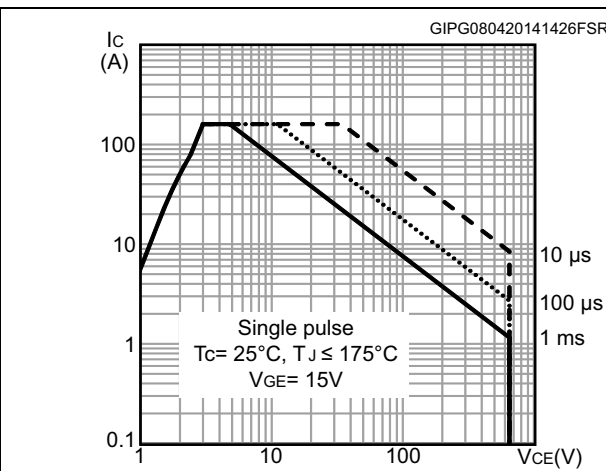


Figure 14. Transfer characteristics

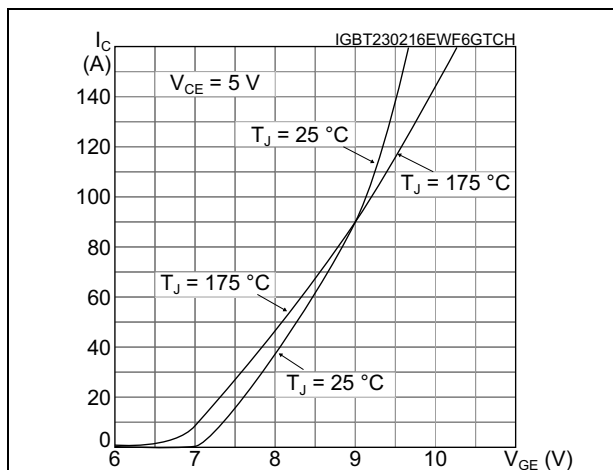


Figure 15. Normalized $V_{GE(th)}$ vs junction temperature

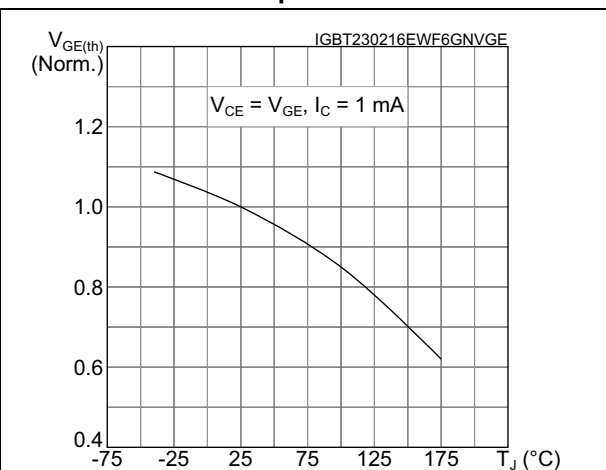


Figure 16. Normalized $V_{(BR)CES}$ vs. junction temperature

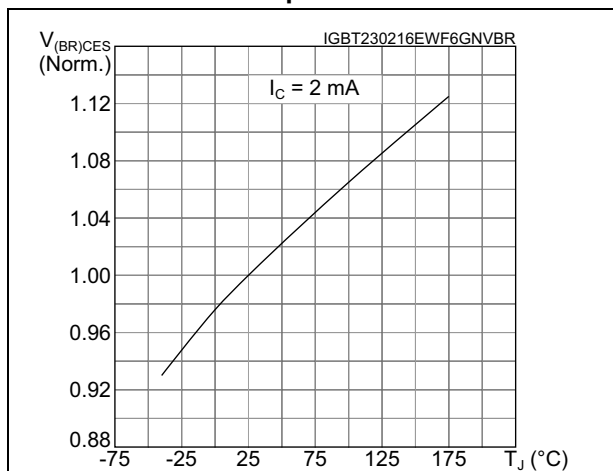


Figure 17. Capacitance variation

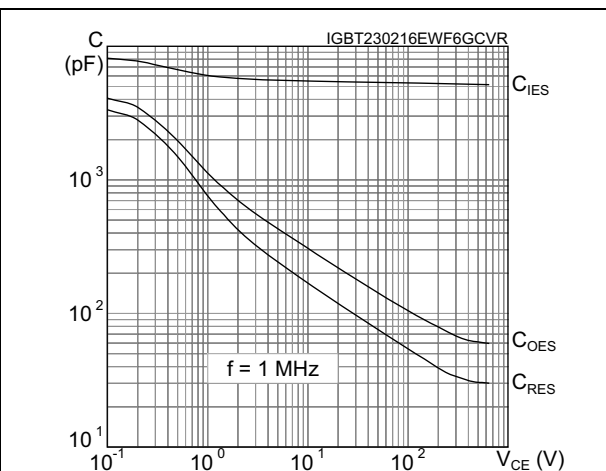


Figure 18. Gate charge vs. gate-emitter voltage

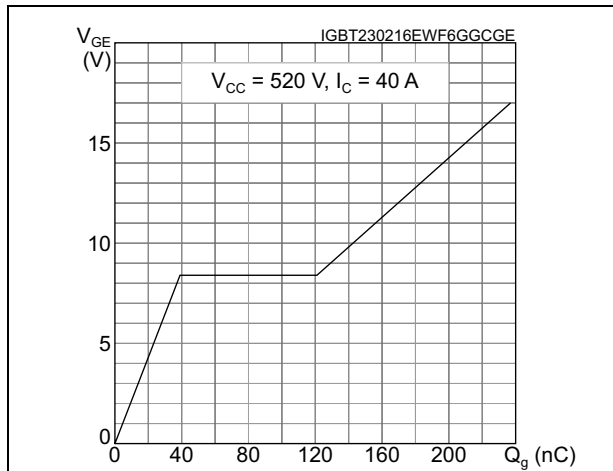


Figure 19. Switching energy vs collector current

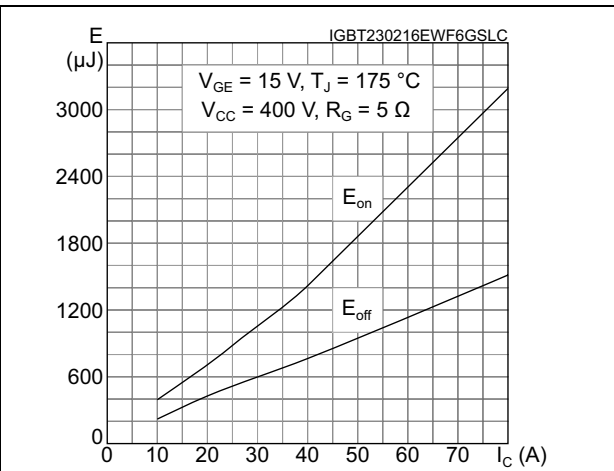


Figure 20. Switching energy vs gate resistance

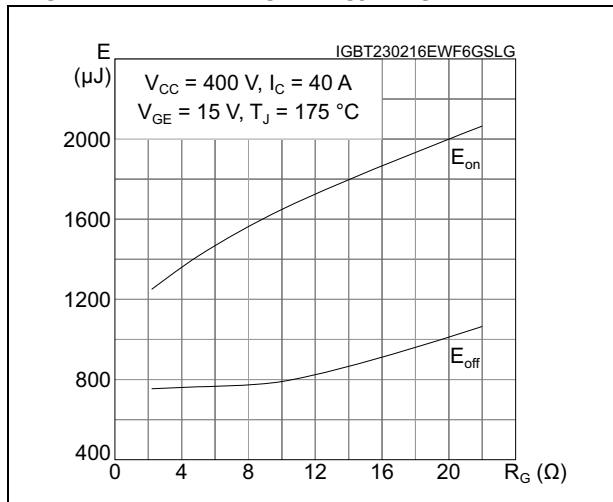


Figure 21. Switching energy vs temperature

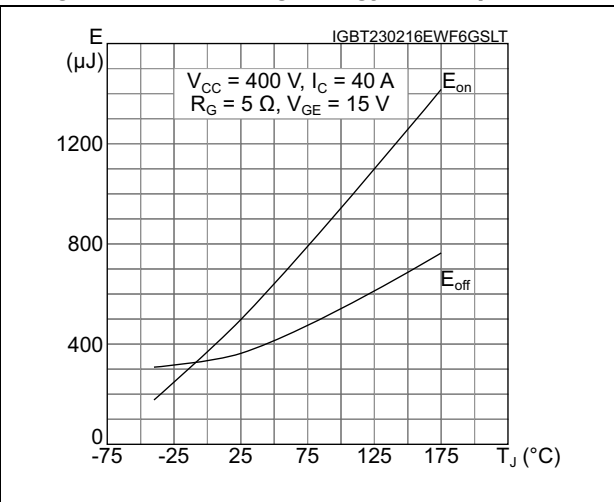


Figure 22. Switching energy collector-emitter voltage

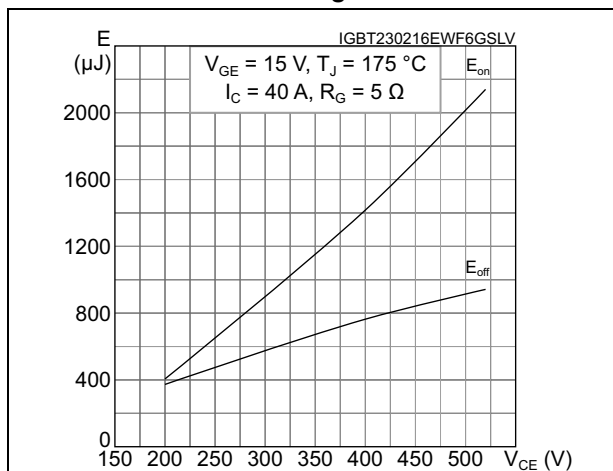


Figure 23. Switching times vs. collector current

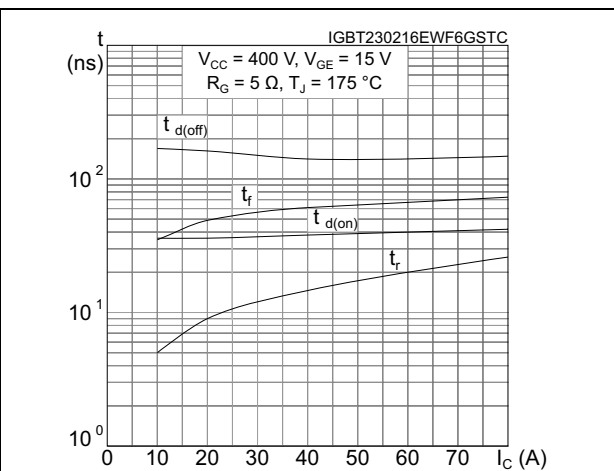


Figure 24. Switching times vs. gate resistance

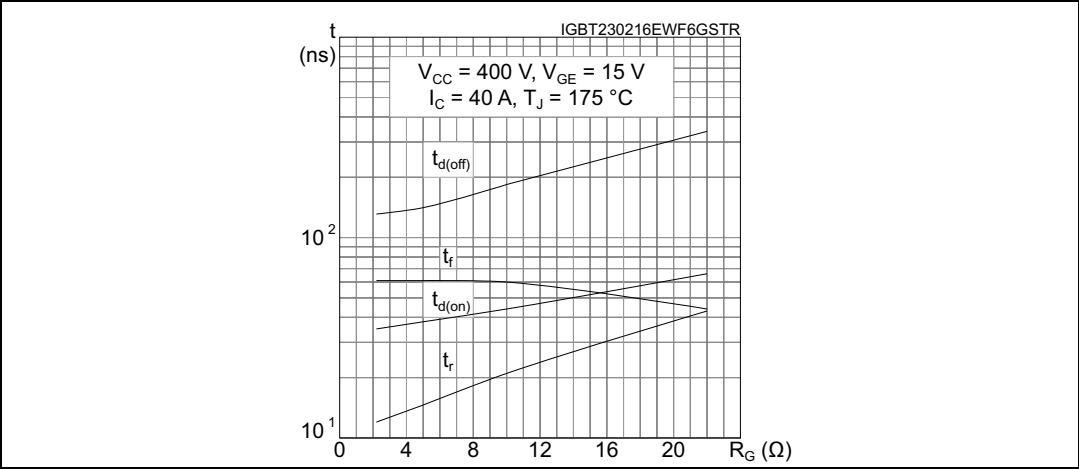
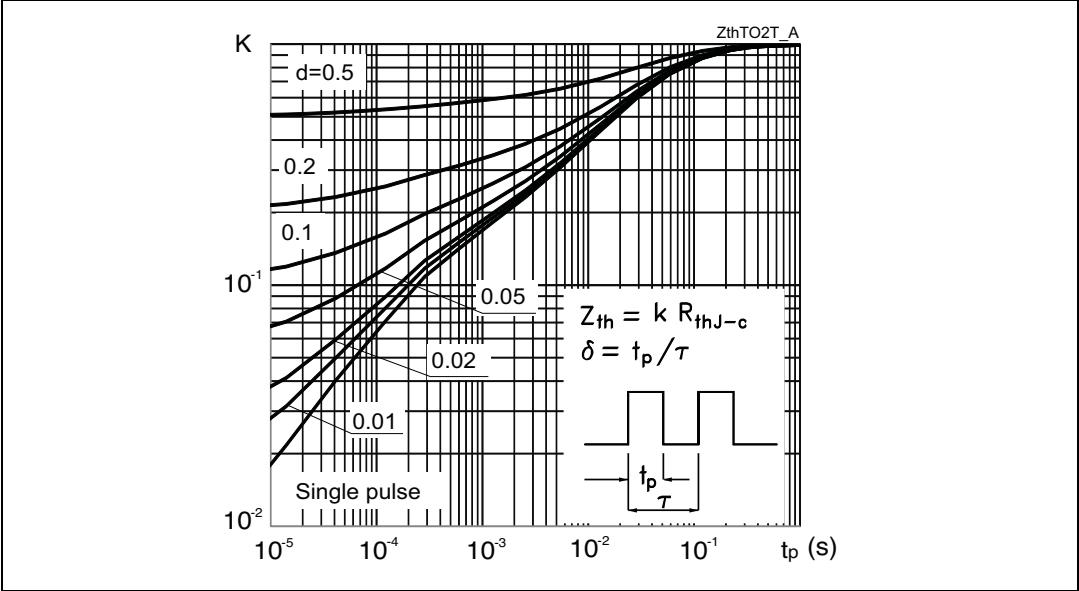


Figure 25. Thermal impedance for TO-247, TO-247 long leads and TO-3P



3 Test circuits

Figure 26. Test circuit for inductive load switching

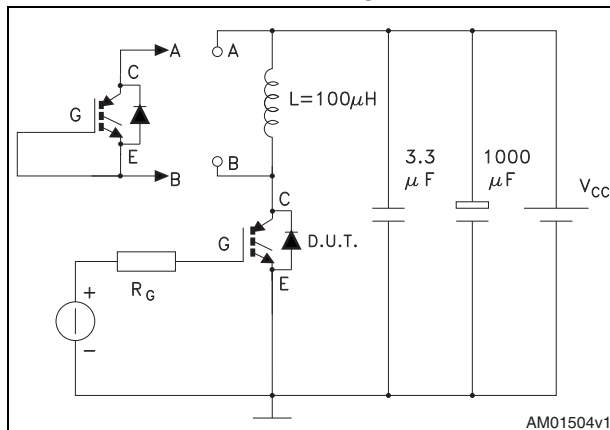


Figure 27. Gate charge test circuit

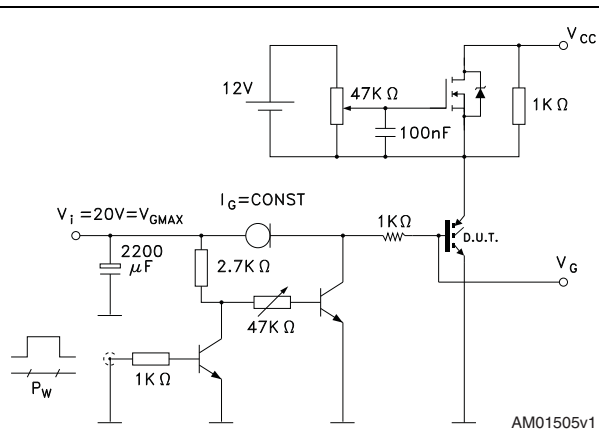
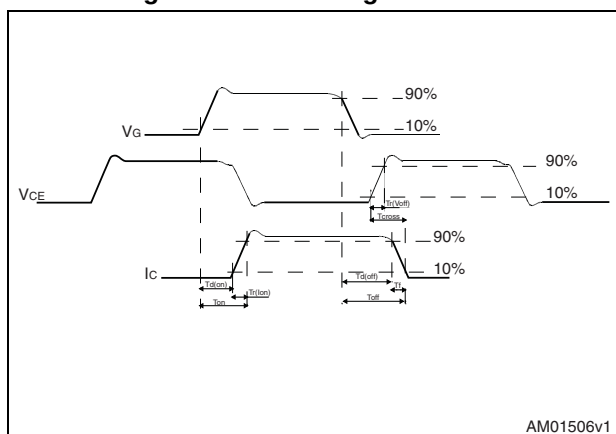


Figure 28. Switching waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-3PF package information

Figure 29. TO-3PF package outline

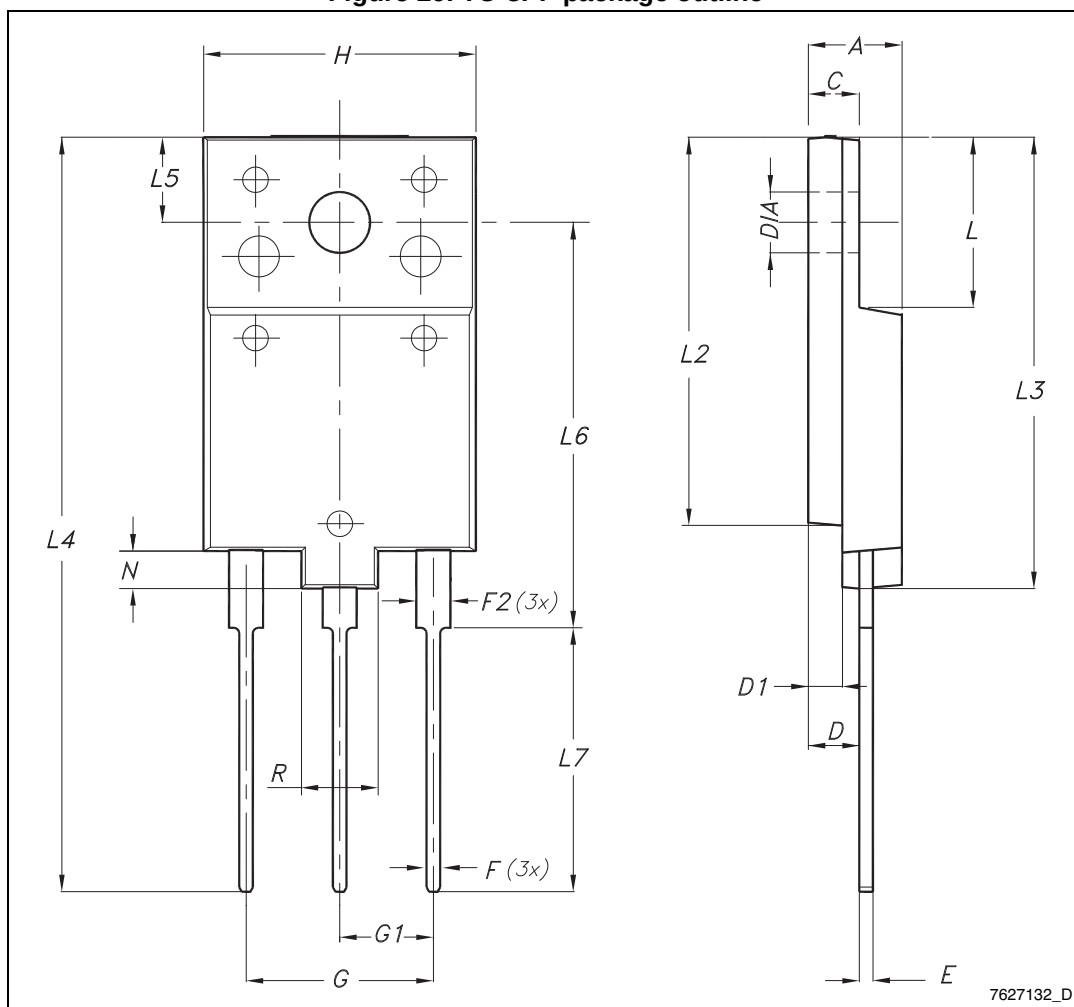


Table 7. TO-3PF mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80

4.2 TO-247, package information

Figure 30. TO-247 package outline

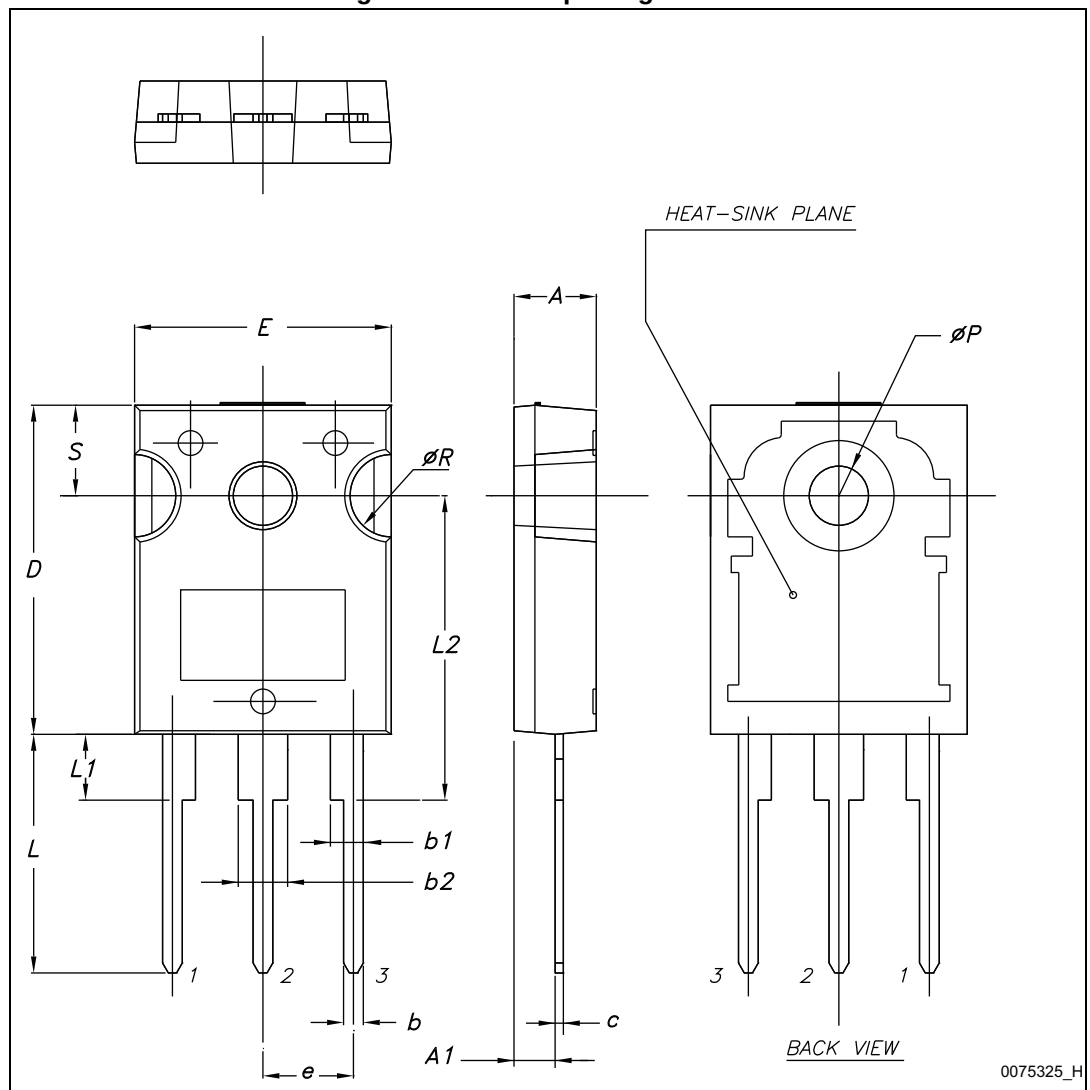


Table 8. TO-247 package mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

4.3 TO-247 long leads, package information

Figure 31. TO-247 long leads package outline

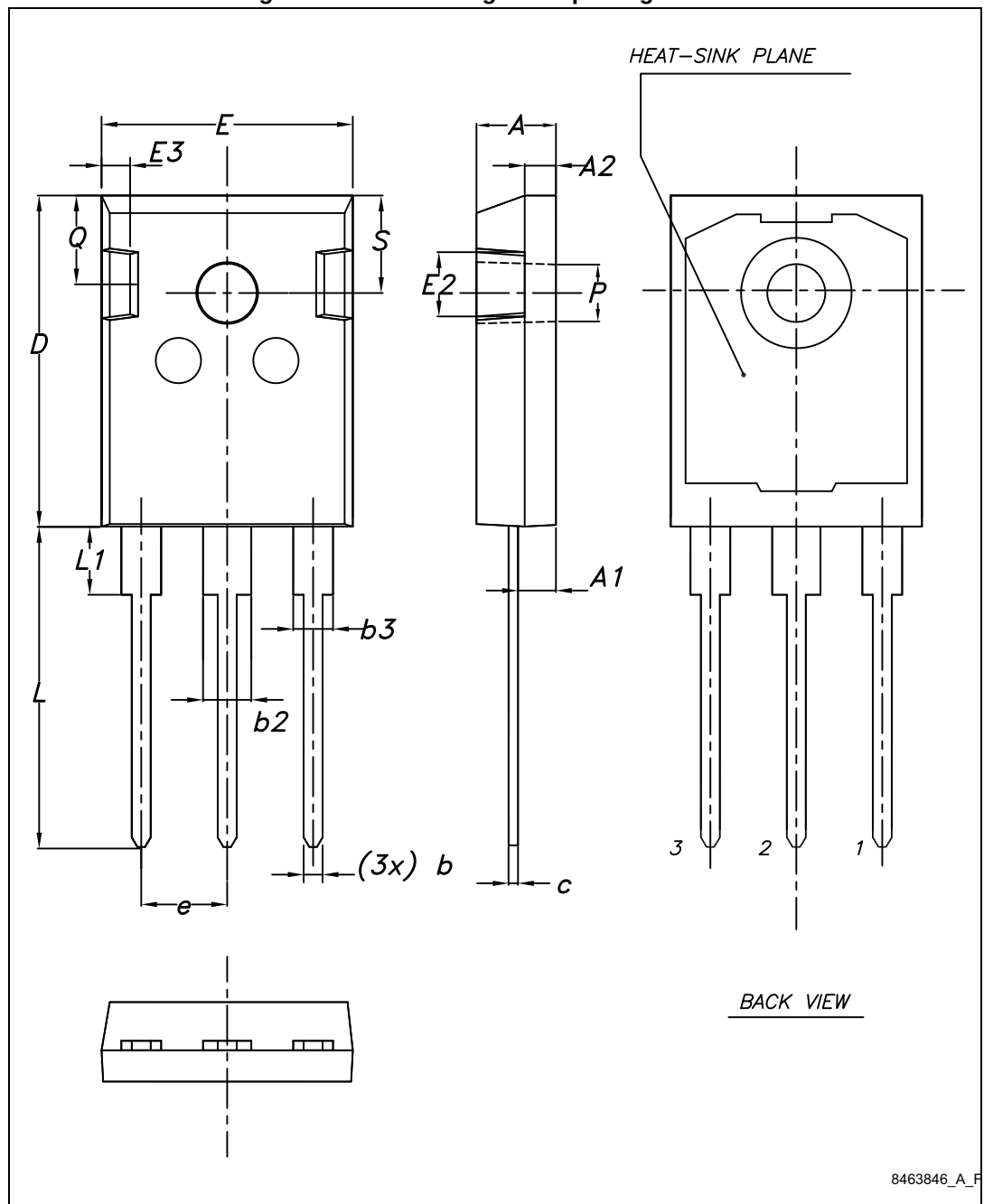


Table 9. TO-247 long leads package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.26
b2			3.25
b3			2.25
c	0.59		0.66
D	20.90	21.00	21.10
E	15.70	15.80	15.90
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	5.34	5.44	5.54
L	19.80	19.92	20.10
L1			4.30
P	3.50	3.60	3.70
Q	5.60		6.00
S	6.05	6.15	6.25

4.4 TO-3P, package information

Figure 32. TO-3P package outline

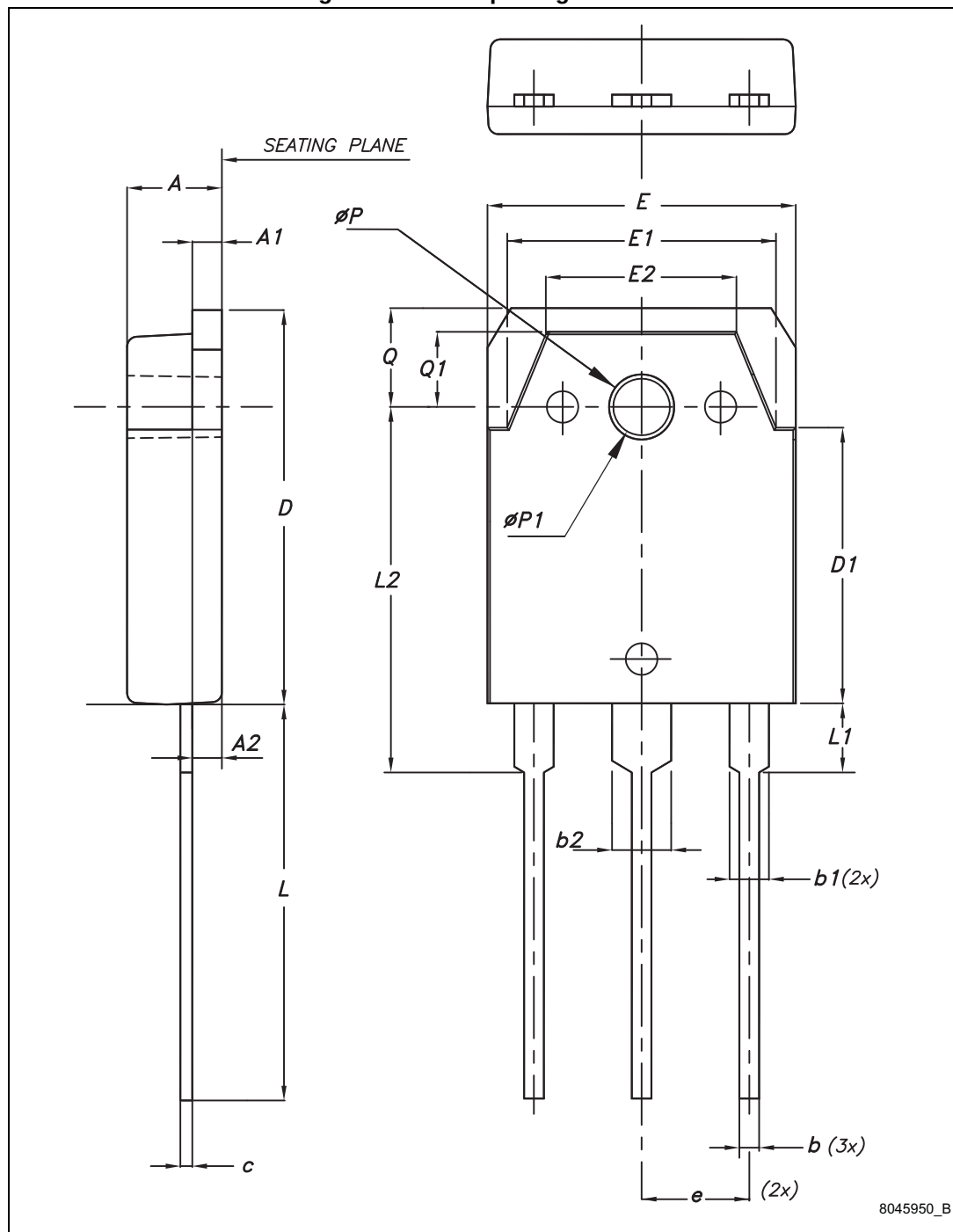


Table 10. TO-3P mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.60	4.80	5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1	13.70	13.90	14.10
E	15.40	15.60	15.80
E1	13.40	13.60	13.80
E2	9.40	9.60	9.90
e	5.15	5.45	5.75
L	19.80	20	20.20
L1	3.30	3.50	3.70
L2	18.20	18.40	18.60
øP	3.30	3.40	3.50
øP1	3.10	3.20	3.30
Q	4.80	5	5.20
Q1	3.60	3.80	4

5 Revision history

Document

Table 11. Document revision history

Date	Revision	Changes
30-Aug-2013	1	Initial release.
11-Sep-2013	2	Document status changed from preliminary to production data. Inserted <i>Section 2.1: Electrical characteristics (curves)</i> .
28-Feb-2014	3	Updated title and description in cover page.
05-Mar-2014	4	Updated units in <i>Table 6: Switching characteristics (inductive load)</i> .
11-Apr-2014	5	Added part number and references for the device in a TO-3PF package.
03-Nov-2016	6	Added device in TO-247 long leads and updated the document accordingly. Updated Section 2.1: Electrical characteristics (curves) and Section 4.3: TO-247 long leads, package information . Minor text changes.

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